

Standard Rectifier

$$V_{RRM} = 800V$$

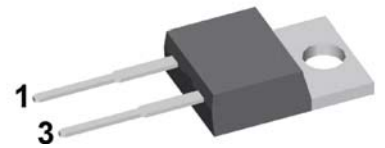
$$I_{FAV} = 30A$$

$$V_F = 1.25V$$

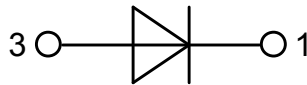
Single Diode

Part number

DSI30-08A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

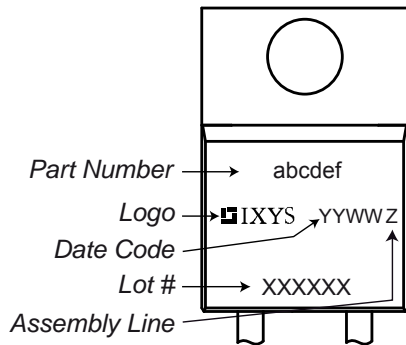
- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

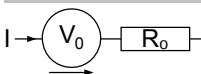
Rectifier				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V
I_R	reverse current, drain current	$V_R = 800 V$	$T_{VJ} = 25^{\circ}C$		40	μA
		$V_R = 800 V$	$T_{VJ} = 150^{\circ}C$		1.5	mA
V_F	forward voltage drop	$I_F = 30 A$	$T_{VJ} = 25^{\circ}C$		1.29	V
		$I_F = 60 A$			1.60	V
		$I_F = 30 A$	$T_{VJ} = 150^{\circ}C$		1.25	V
		$I_F = 60 A$			1.66	V
I_{FAV}	average forward current	$T_C = 130^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$		30	A
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$		0.82	V
r_F	slope resistance				14.1	m Ω
R_{thJC}	thermal resistance junction to case				0.9	K/W
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		160	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		300	A
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		325	A
		$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		255	A
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		275	A
I^2t	value for fusing	$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		450	A ² s
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		440	A ² s
		$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		325	A ² s
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		315	A ² s
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		10	pF

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{stg}	storage temperature		-55		150	°C
T_{vj}	virtual junction temperature		-40		175	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking


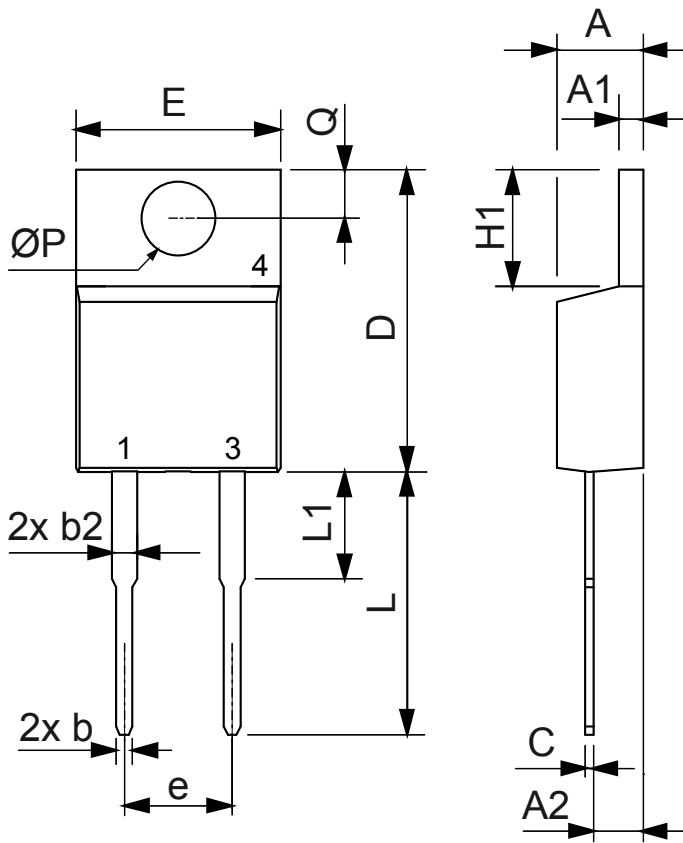
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSI30-08A	DSI30-08A	Tube	50	476382

Similar Part	Package	Voltage class
DSI30-08AS	TO-263AB (D2Pak) (2)	800
DSI30-08AC	ISOPLUS220AC (2)	800
DSI30-12A	TO-220AC (2)	1200
DSI30-12AS	TO-263AB (D2Pak) (2)	1200
DSI30-12AC	ISOPLUS220AC (2)	1200
DSI30-16A	TO-220AC (2)	1600
DSI30-16AS	TO-263AB (D2Pak) (2)	1600

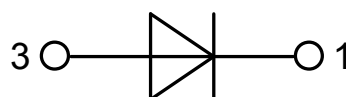
Equivalent Circuits for Simulation
** on die level*
 $T_{vj} = 175^{\circ}C$

Rectifier

$V_{0\ max}$	threshold voltage	0.82	V
$R_{0\ max}$	slope resistance *	11	mΩ

Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



Rectifier

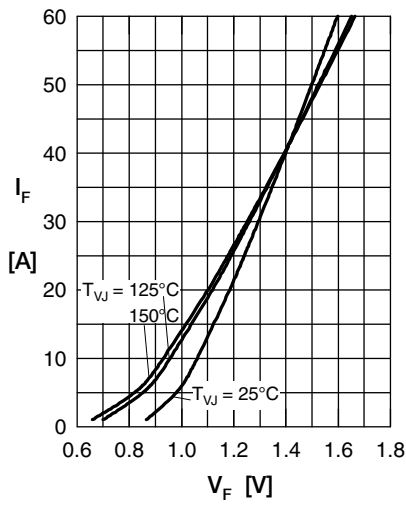


Fig. 1 Forward current versus voltage drop per diode

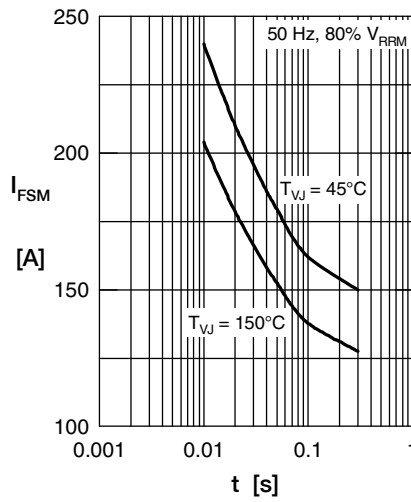


Fig. 2 Surge overload current

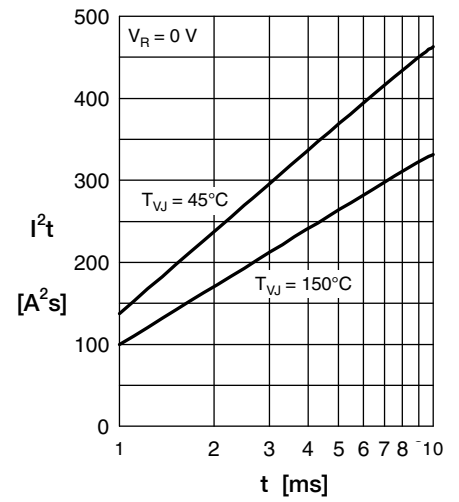


Fig. 3 I^2t versus time per diode

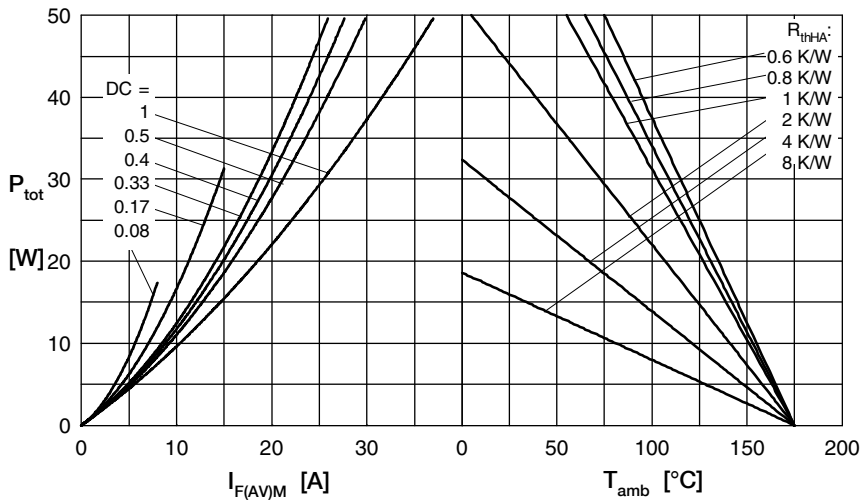


Fig. 4 Power dissipation vs. direct output current and ambient temperature

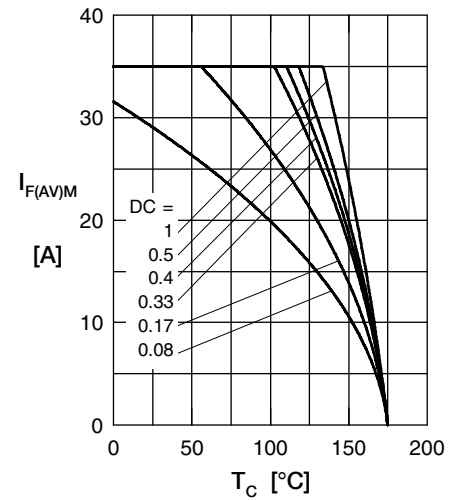


Fig. 5 Max. forward current vs. case temperature

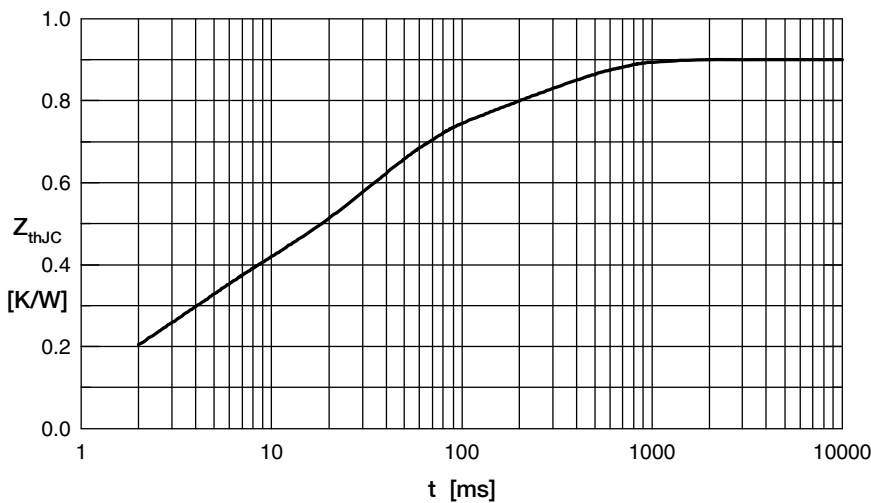


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.03	0.0004
2	0.08	0.002
3	0.2	0.003
4	0.39	0.03
5	0.2	0.29